

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

1. - 11. (Canceled)

12. (Currently Amended) A printing mask comprising a mask frame and a mesh extended on the mask frame, wherein the printing mask includes

a first resin layer that is formed inside the mesh, wherein a thickness of the first resin layer is equivalent to a thickness of the mesh;

a second resin layer that is formed directly on a surface of the first resin layer, wherein thickness of the second resin layer is 3 micrometers or less;

a pattern forming portion in which the second resin layer is not formed, wherein the pattern forming portion is located in a region corresponding to an electrode pattern to be formed on a printing object;

a mask portion in which the first resin layer and the second resin layer are formed, wherein the mask portion is located in a region other than the region of the pattern forming portion; and

a peripheral portion in which the first resin layer is formed, but the second resin layer is not formed, wherein the peripheral portion is located within the pattern forming portion and along a periphery of the pattern forming portion.

13. (Previously Presented) The printing mask according to claim 12, wherein the peripheral portion is located within a range corresponding to a width of a bulge from an end of the electrode pattern, which is formed at the end of the electrode pattern on forming the electrode pattern.

14. (Previously Presented) The printing mask according to claim 12, wherein the peripheral portion has a width of equal to or smaller than 0.2 millimeter, and is located within a range not less than 0.1 millimeter and not more than 0.5 millimeter from the periphery of the pattern forming portion.

15. (Previously Presented) A solar cell comprising:

- a semiconductor layer formed on a semiconductor substrate having a p-n junction in parallel with a substrate surface;
- a front silver electrode formed in a predetermined shape on a surface of the semiconductor layer;
- a back aluminum electrode formed on a back surface of the semiconductor layer so that a part of the semiconductor layer is exposed; and
- a back silver electrode formed to cover an exposed part that is not covered by the back aluminum electrode on the semiconductor layer and a part of the back aluminum electrode arranged adjacent to the exposed part, wherein
 - the back aluminum electrode is formed with the printing mask according to claim 12, and
 - a difference in average film thickness between a bulge at an edge part and other parts of the back aluminum electrode is equal to or less than 5 micrometers.